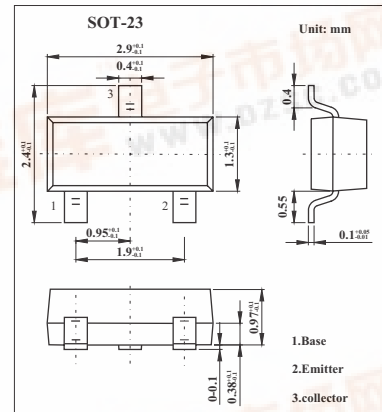


SMD Type Transistors

PNP Silicon AF Transistors  
KC807(BC807)

■ Features

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-50	V
Collector-emitter voltage	V <sub>CE0</sub>	-45	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current (DC)	I <sub>c</sub>	-800	mA
power dissipation	P <sub>d</sub>	310	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = -10 μA, V <sub>BE</sub> = 0	-50			V
Collector-to-emitter breakdown voltage	V <sub>CE0</sub>	I <sub>c</sub> = -10 mA, I <sub>b</sub> = 0	-45			V
Emitter-to-base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -10 μA, I <sub>c</sub> = 0	-5			V
Collector cutoff current	I <sub>CES</sub>	V <sub>CB</sub> = -25 V, V <sub>BE</sub> = 0			-100	nA
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> = -4 V, I <sub>c</sub> = 0			-100	nA
DC current gain *	h <sub>FE</sub>	I <sub>c</sub> = -100 mA, V <sub>CE</sub> = -1 V	100		630	
		I <sub>c</sub> = -300 mA, V <sub>CE</sub> = -1 V	60			
Collector saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> = -500 mA, I <sub>b</sub> = -50 mA			-0.7	V
Base emitter on voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = -1V, I <sub>c</sub> = 300mA			-1.2	V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, f = 1MHz			12	pF
Transition frequency	f <sub>T</sub>	I <sub>c</sub> = -10 mA, V <sub>CE</sub> = -5 V, f = 50 MHz		100		MHz

\* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

■ Marking

NO.	KC807-16	KC807-25	KC807-40
Marking	9FA	9FB	9FC
hFE	100~250	160~400	250~630

